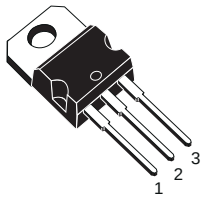
STP80NF55L-08
STB80NF55L-08

N-CHANNEL 55V - 0.0065Ω - 80A - TO-220/D²PAK
STripFET™ II POWER MOSFET

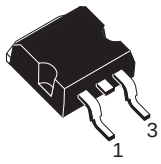
PRELIMINARY DATA

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STP80NF55L-08	55 V	0.008Ω	80 A
STB80NF55L-08	55 V	0.008Ω	80 A

- TYPICAL R_{DS}(on) = 0.0065Ω
- LOW THRESHOLD DRIVE
- LOGIC LEVEL DEVICE



TO-220

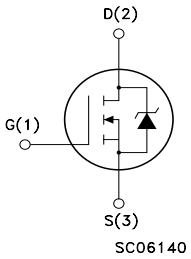


D²PAK

DESCRIPTION

This Power Mosfet is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalance characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

INTERNAL SCHEMATIC DIAGRAM



APPLICATIONS

- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC CONVERTERS
- AUTOMOTIVE ENVIRONMENT

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	55	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	55	V
V_{GS}	Gate- source Voltage	± 16	V
I_D (1)	Drain Current (continuos) at T_C = 25°C	80	A
I_D (1)	Drain Current (continuos) at T_C = 100°C	80	A
I_{DM} (●)	Drain Current (pulsed)	320	A
P_{TOT}	Total Dissipation at T_C = 25°C	300	W
	Derating Factor	2	W/°C
dv/dt (2)	Peak Diode Recovery voltage slope	15	V/ns
E_{AS}(3)	Single Pulse Avalanche Energy	870	mJ
T_{stg}	Storage Temperature	–55 to 175	°C
T_j	Max. Operating Junction Temperature	175	°C

(●) Pulse width limited by safe operating area

(1) Current Limited by Package
(2) I_{SD} ≤80A, di/dt ≤500A/µs, V_{DD} =40V $T_j \le T_{JMAX.}$
(3) Starting T_j=25°C, I_D=40A, V_{DD}=40V

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	0.5	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300	°C

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	55			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating			1	µA
		V_{DS} = Max Rating, T_C = 125 °C			10	µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 16V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	1	1.6	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V, I_D = 40 A		0.0065	0.008	Ω
		V_{GS} = 5 V, I_D = 40 A		0.008	0.01	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs}	Forward Transconductance	V_{DS} =15V, I_D =40 A		150		S
C_{iss}	Input Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		4350		pF
C_{oss}	Output Capacitance			800		pF
C_{rss}	Reverse Transfer Capacitance			260		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 27V, I_D = 40A		35		ns
t_r	Rise Time	R_G = 4.7Ω V_{GS} = 4.5V (see test circuit, Figure 3)		145		ns
Q_g	Total Gate Charge	V_{DD} = 27.5 V, I_D = 80A,		75	100	nC
Q_{gs}	Gate-Source Charge	V_{GS} = 4.5V		20		nC
Q_{gd}	Gate-Drain Charge			30		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	V_{DD} = 27V, I_D = 40A,		85		ns
t_f	Fall Time	R_G = 4.7Ω, V_{GS} = 4.5V (see test circuit, Figure 3)		65		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				80	A
I_{SDM} (2)	Source-drain Current (pulsed)				320	A
V_{SD} (2)	Forward On Voltage	I_{SD} = 80A, V_{GS} = 0			1.5	V
t_{rr}	Reverse Recovery Time	I_{SD} = 80A, di/dt = 100A/µs,		85		ns
Q_{rr}	Reverse Recovery Charge	V_{DD} = 20V, T_j = 150°C		280		nC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		6.5		A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

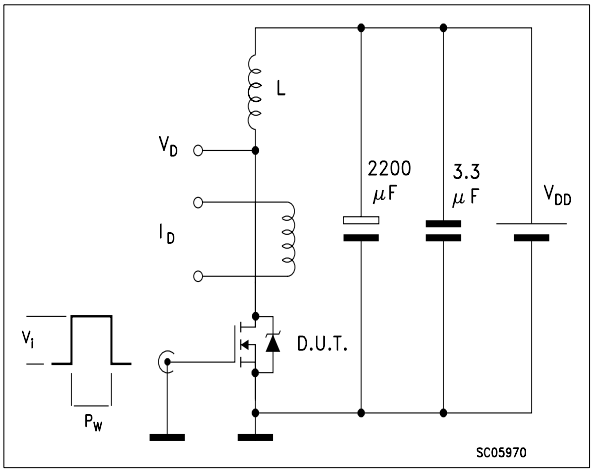


Fig. 2: Unclamped Inductive Waveform

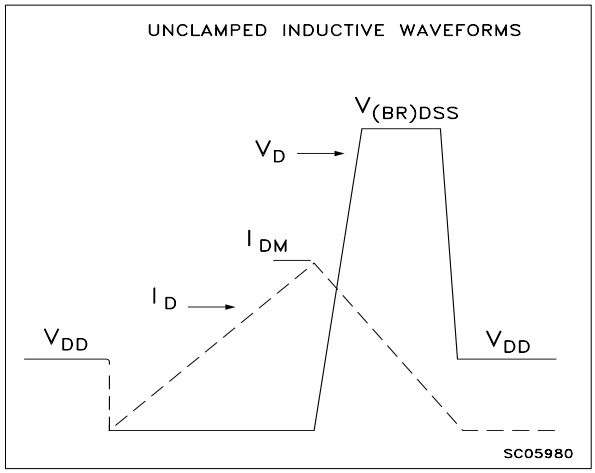


Fig. 3: Switching Times Test Circuit For Resistive Load

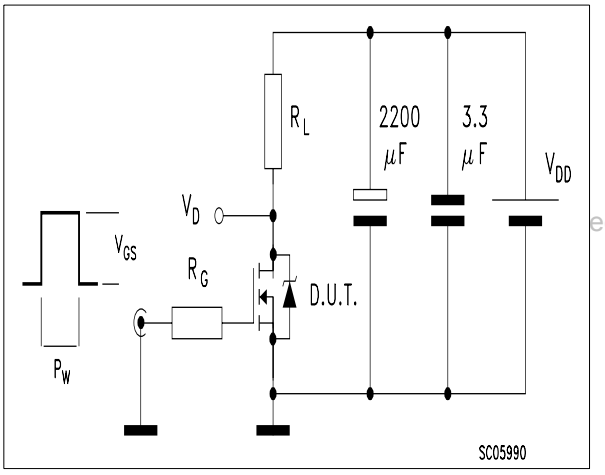


Fig. 4: Gate Charge test Circuit

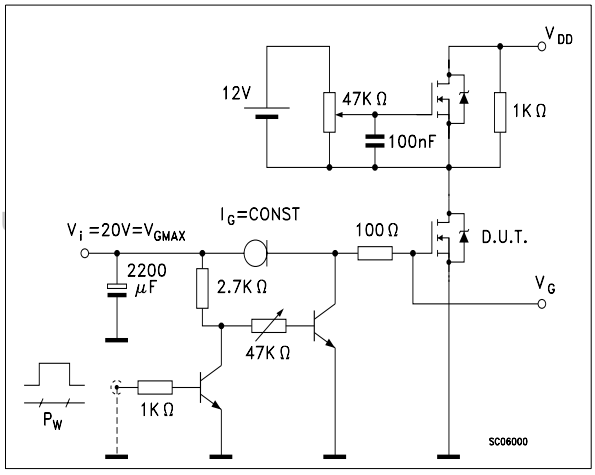
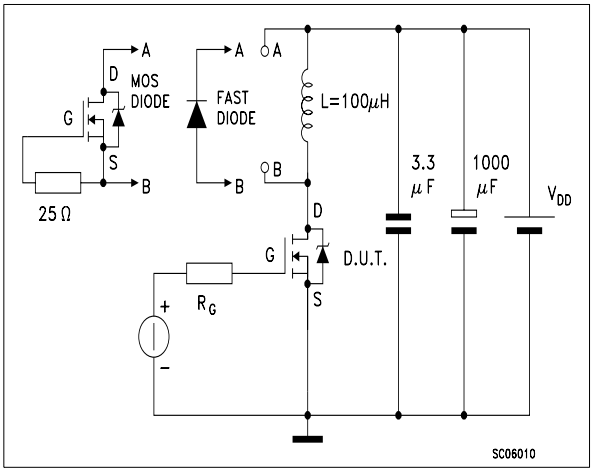
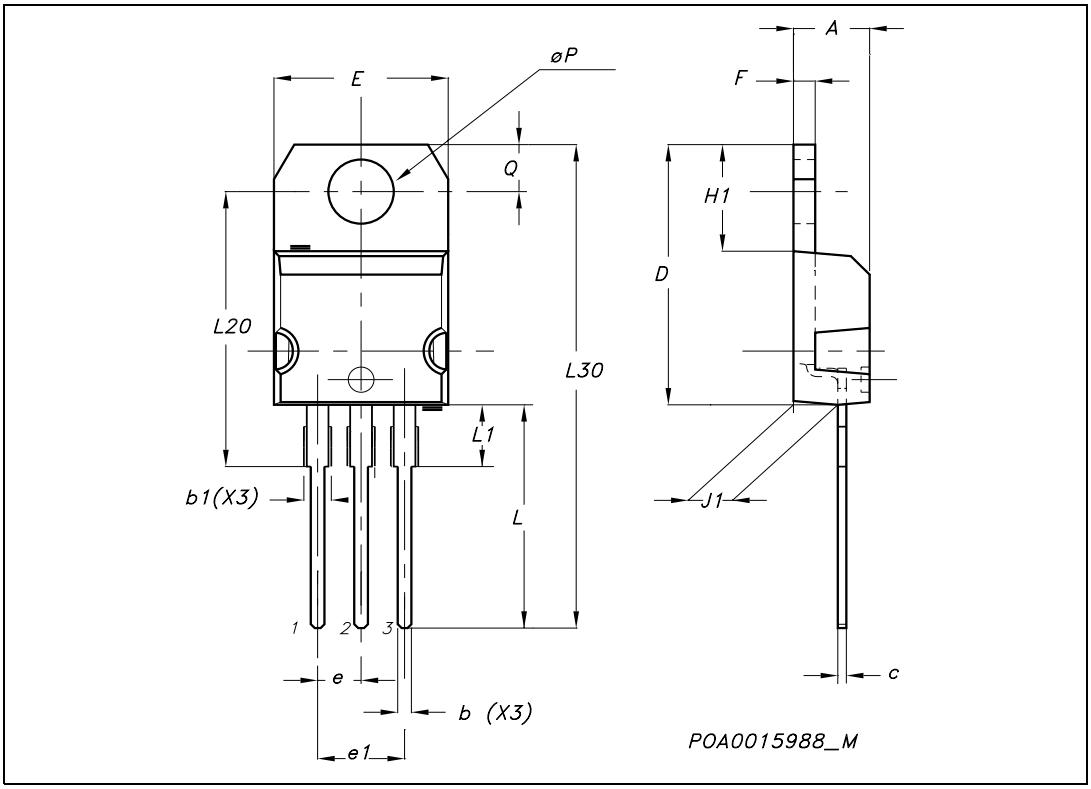


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



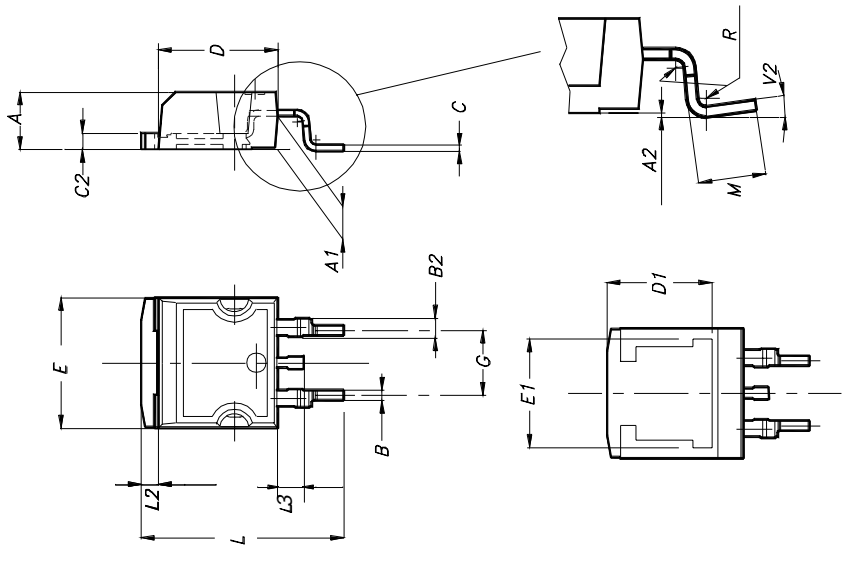
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116

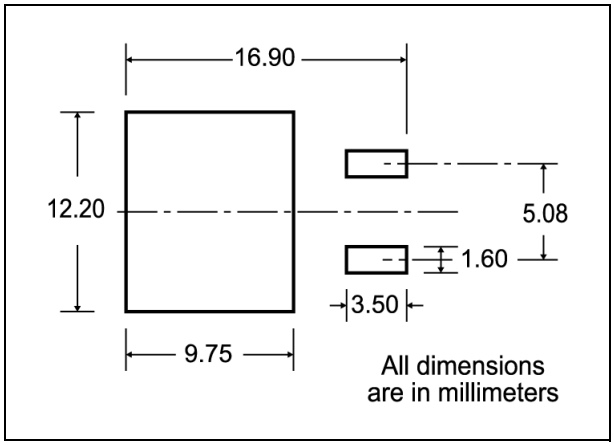


D²PAK MECHANICAL DATA

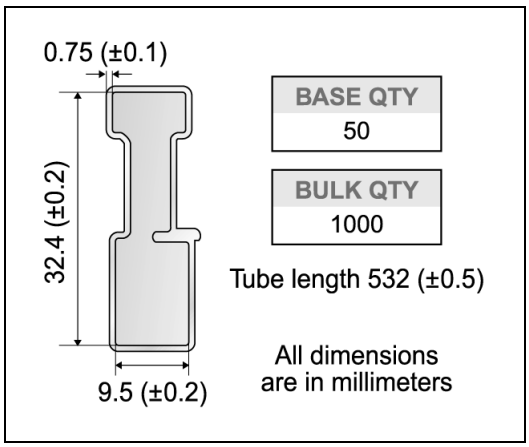
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		4º			



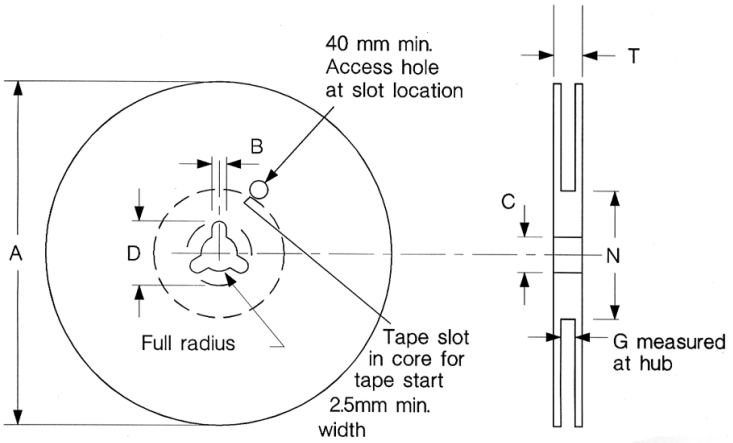
D²PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



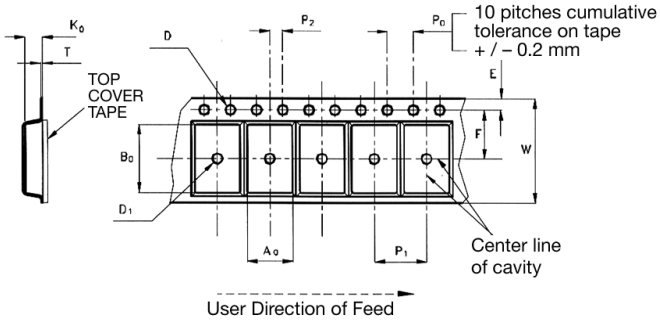
REEL MECHANICAL DATA

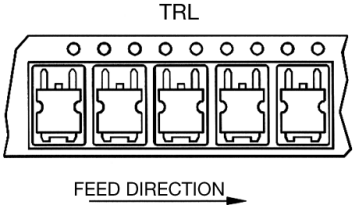
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

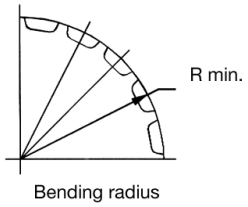
BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956







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